

# Complementary Plastic Silicon Power Transistors

... designed for low power audio amplifier and low-current, high speed switching applications.

- High Collector-Emitter Sustaining Voltage —  
 $V_{CE(sus)} = 80 \text{ Vdc (Min) — BD789, BD790}$   
 $= 100 \text{ Vdc (Min) — BD791, BD792}$
- High DC Current Gain @  $I_C = 200 \text{ mAdc}$   
 $h_{FE} = 40-250$
- Low Collector-Emitter Saturation Voltage —  
 $V_{CE(sat)} = 0.5 \text{ Vdc (Max) @ } I_C = 500 \text{ mAdc}$
- High Current Gain — Bandwidth Product —  
 $f_T = 40 \text{ MHz (Min) @ } I_C = 100 \text{ mAdc}$

## \*MAXIMUM RATINGS

Rating	Symbol	BD789 BD790	BD791 BD792	Unit
Collector-Emitter Voltage	$V_{CEO}$	80	100	Vdc
Collector-Base Voltage	$V_{CB}$	80	100	Vdc
Emitter-Base Voltage	$V_{EBO}$	6.0		Vdc
Collector Current — Continuous — Peak	$I_C$	4.0 8.0		Adc
Base Current	$I_B$	1.0		Adc
Total Power Dissipation @ $T_C = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	15 0.12		Watts W/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	$T_J, T_{stg}$	-65 to +150		$^\circ\text{C}$

## THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	8.34	$^\circ\text{C/W}$

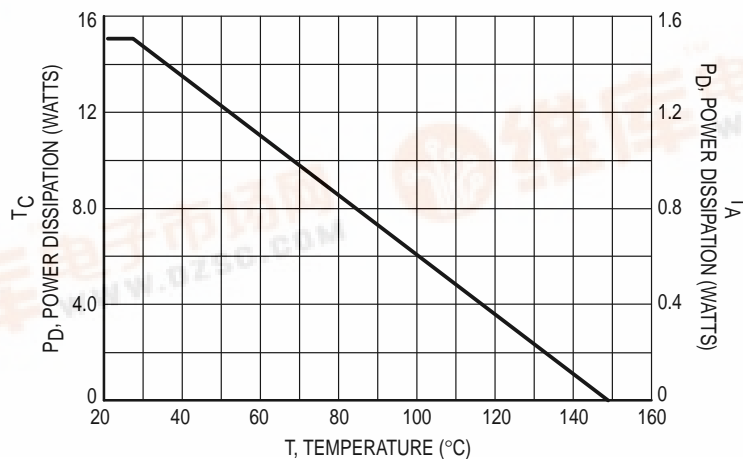


Figure 1. Power Derating

**NPN**  
**BD789**  
**BD791\***  
**PNP**  
**BD790**  
**BD792\***

\*Motorola Preferred Device

**4 AMPERE**  
**POWER TRANSISTORS**  
**COMPLEMENTARY**  
**SILICON**  
**80, 100 VOLTS**  
**15 WATTS**

**CASE 77-08**  
**TO-225AA TYPE**

## BD789 BD791 BD790 BD792

\*ELECTRICAL CHARACTERISTICS ( $T_C = 25^\circ\text{C}$  unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit	
<b>OFF CHARACTERISTICS</b>					
Collector–Emitter Sustaining Voltage (1) ( $I_C = 10\text{ mA}$ , $I_B = 0$ )	BD789, BD790 BD791, BD792	$V_{CE(sus)}$	80 100	— —	Vdc
Collector Cutoff Current ( $V_{CE} = 40\text{ Vdc}$ , $I_B = 0$ ) ( $V_{CE} = 50\text{ Vdc}$ , $I_B = 0$ )	BD789, BD790 BD791, BD792	$I_{CEO}$	— —	100 100	$\mu\text{Adc}$
Collector Cutoff Current ( $V_{CE} = 80\text{ Vdc}$ , $V_{BE(off)} = 1.5\text{ Vdc}$ ) ( $V_{CE} = 100\text{ Vdc}$ , $V_{BE(off)} = 1.5\text{ Vdc}$ ) ( $V_{CE} = 40\text{ Vdc}$ , $V_{BE(off)} = 1.5\text{ Vdc}$ , $T_C = 125^\circ\text{C}$ ) ( $V_{CE} = 50\text{ Vdc}$ , $V_{BE(off)} = 1.5\text{ Vdc}$ , $T_C = 125^\circ\text{C}$ )	BD789, BD790 BD791, BD792 BD789, BD790 BD791, BD792	$I_{CEX}$	— — — —	1.0 1.0 0.1 0.1	$\mu\text{Adc}$   $\text{mA}$
Emitter Cutoff Current ( $V_{EB} = 6.0\text{ Vdc}$ , $I_C = 0$ )		$I_{EBO}$	—	1.0	$\mu\text{Adc}$

### ON CHARACTERISTICS (1)

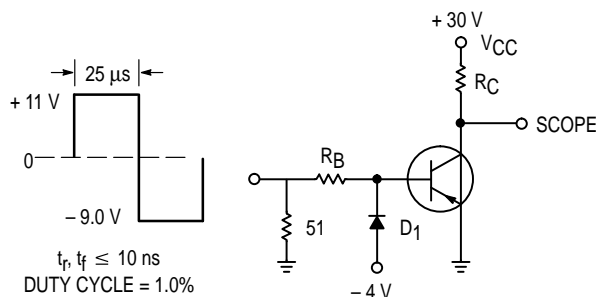
DC Current Gain ( $I_C = 200\text{ mA}$ , $V_{CE} = 3.0\text{ Vdc}$ ) ( $I_C = 1.0\text{ Adc}$ , $V_{CE} = 3.0\text{ Vdc}$ ) ( $I_C = 2.0\text{ Adc}$ , $V_{CE} = 3.0\text{ Vdc}$ ) ( $I_C = 4.0\text{ Adc}$ , $V_{CE} = 3.0\text{ Vdc}$ )		$h_{FE}$	40 20 10 5.0	250 — — —	—
Collector Emitter Saturation Voltage ( $I_C = 500\text{ mA}$ , $I_B = 50\text{ mA}$ ) ( $I_C = 1.0\text{ Adc}$ , $I_B = 100\text{ mA}$ ) ( $I_C = 2.0\text{ Adc}$ , $I_B = 200\text{ mA}$ ) ( $I_C = 4.0\text{ Adc}$ , $I_B = 800\text{ mA}$ )		$V_{CE(sat)}$	— — — —	0.5 1.0 2.5 3.0	Vdc
Base–Emitter Saturation Voltage ( $I_C = 2.0\text{ Adc}$ , $I_B = 200\text{ mA}$ )		$V_{BE(sat)}$	—	1.8	Vdc
Base–Emitter On Voltage ( $I_C = 200\text{ mA}$ , $V_{CE} = 3.0\text{ Vdc}$ )		$V_{BE(on)}$	—	1.5	Vdc

### DYNAMIC CHARACTERISTICS

Current–Gain — Bandwidth Product ( $I_C = 100\text{ mA}$ , $V_{CE} = 10\text{ Vdc}$ , $f = 10\text{ MHz}$ )		$f_T$	40	—	MHz
Output Capacitance ( $V_{CB} = 10\text{ Vdc}$ , $I_C = 0$ , $f = 0.1\text{ MHz}$ )	BD789, BD791 BD790, BD792	$C_{ob}$	— —	50 70	pF
Small–Signal Current Gain ( $I_C = 200\text{ mA}$ , $V_{CE} = 10\text{ Vdc}$ , $f = 1.0\text{ kHz}$ )		$h_{fe}$	10	—	—

\* Indicates JEDEC Registered Data.

(1) Pulse Test: Pulse Width  $\leq 300\ \mu\text{s}$ , Duty Cycle  $\leq 2.0\%$ .



$R_B$  AND  $R_C$  VARIED TO OBTAIN DESIRED CURRENT LEVELS

$D_1$  MUST BE FAST RECOVERY TYPE, eg

MBR340 USED ABOVE  $I_B \approx 100\text{ mA}$

MSD6100 USED BELOW  $I_B \approx 100\text{ mA}$

FOR PNP TEST CIRCUIT, REVERSE ALL POLARITIES.

Figure 2. Switching Time Test Circuit

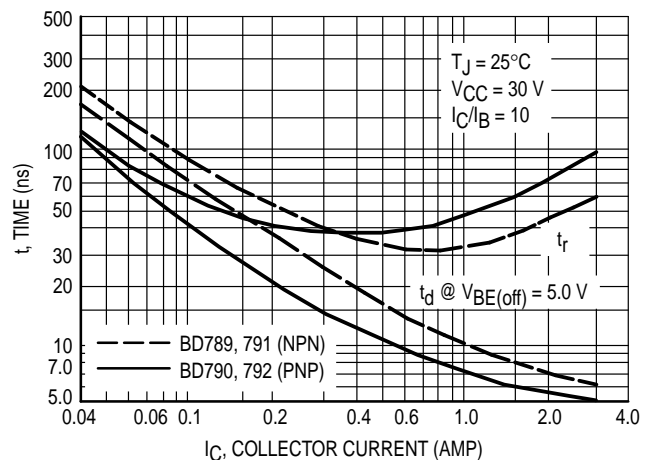


Figure 3. Turn–On Time

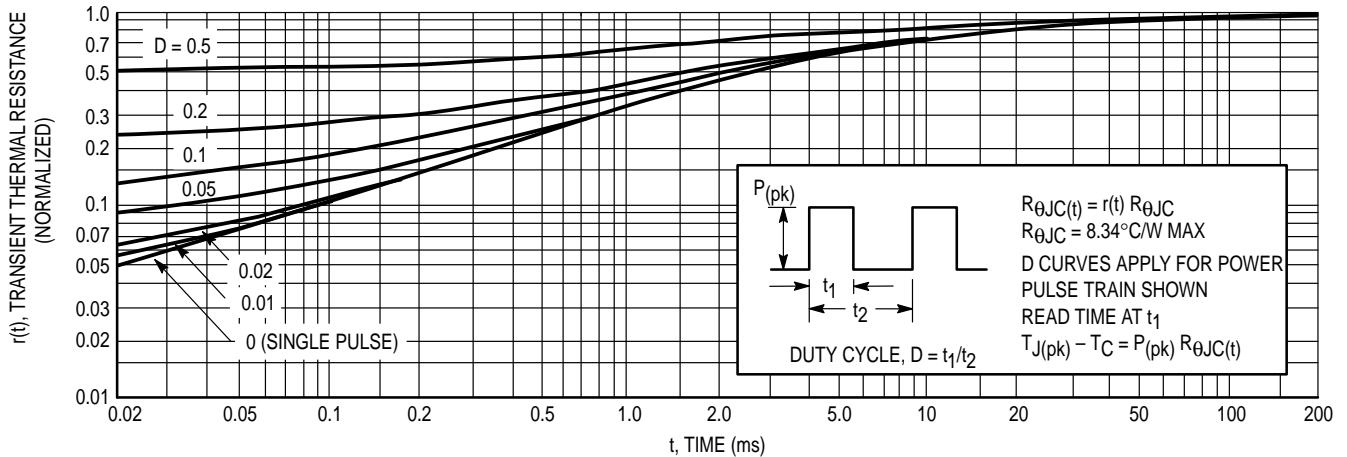


Figure 4. Thermal Response

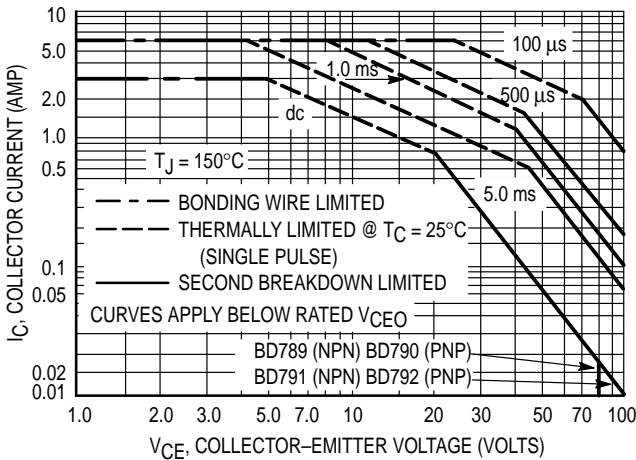


Figure 5. Active Region Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate  $I_C - V_{CE}$  limits of the transistor that must be observed for reliable operation, i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 5 is based on  $T_J(pk) = 150^\circ\text{C}$ :  $T_C$  is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided  $T_J(pk) \leq 150^\circ\text{C}$ ,  $T_J(pk)$  may be calculated from the data in Figure 4. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

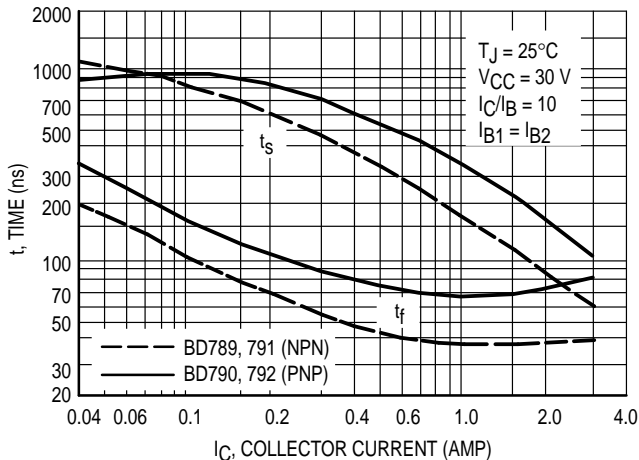


Figure 6. Turn-Off Time

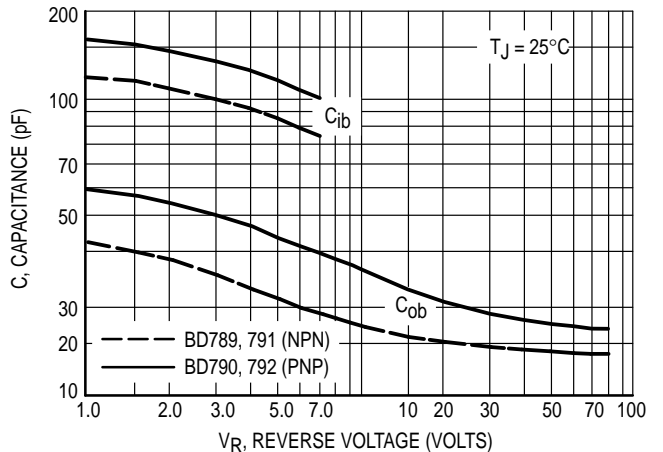
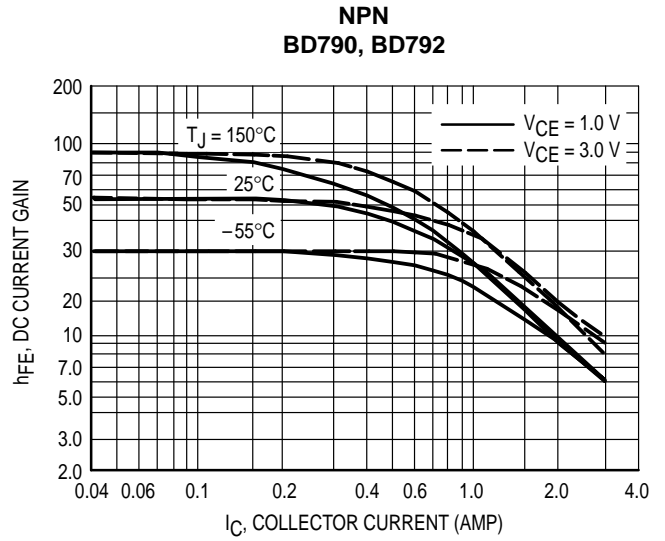
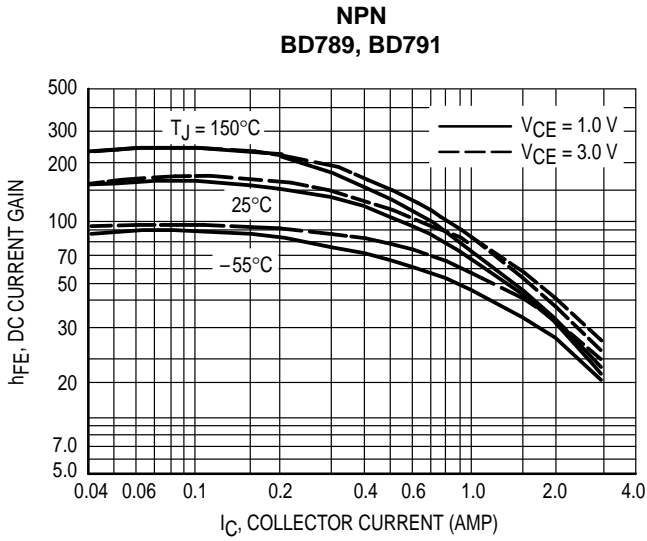
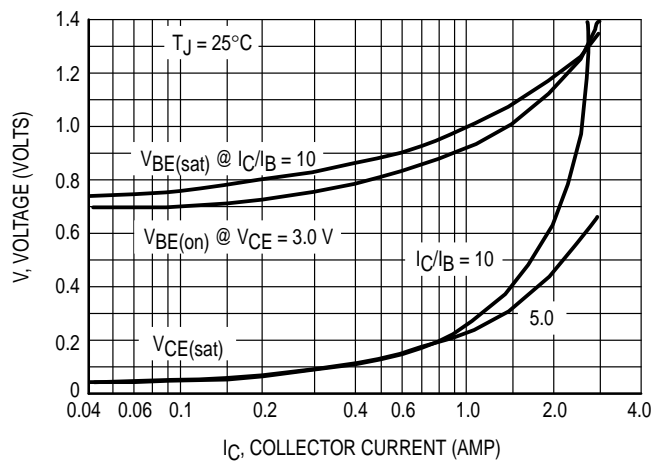
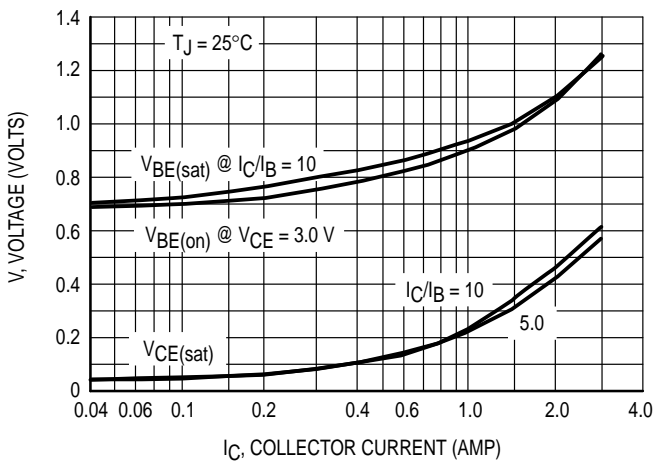


Figure 7. Capacitance

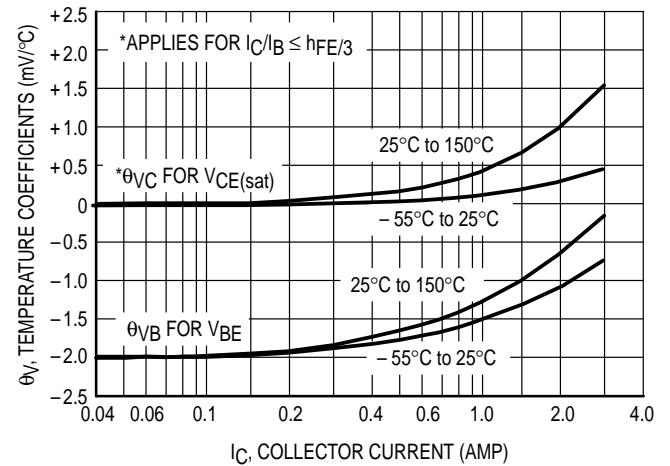
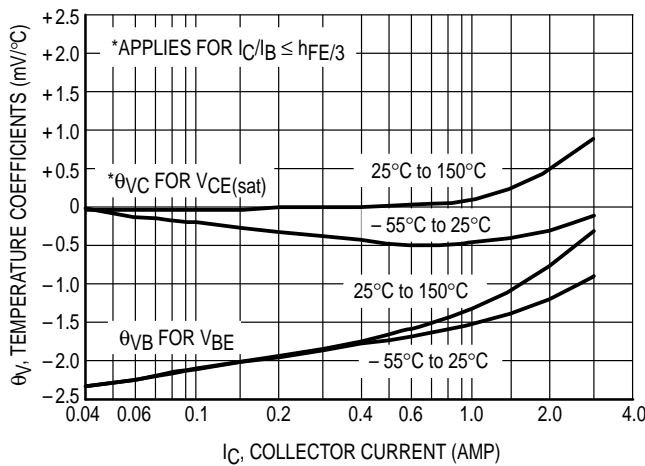
**BD789 BD791 BD790 BD792**



**Figure 8. DC Current Gain**



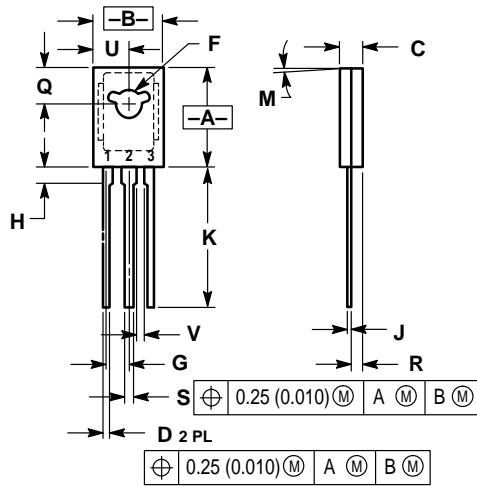
**Figure 9. "On" Voltages**



**Figure 10. Temperature Coefficients**

**BD789 BD791 BD790 BD792**

**PACKAGE DIMENSIONS**




- NOTES:  
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.  
 2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.425	0.435	10.80	11.04
B	0.295	0.305	7.50	7.74
C	0.095	0.105	2.42	2.66
D	0.020	0.026	0.51	0.66
F	0.115	0.130	2.93	3.30
G	0.094 BSC		2.39 BSC	
H	0.050	0.095	1.27	2.41
J	0.015	0.025	0.39	0.63
K	0.575	0.655	14.61	16.63
M	5° TYP		5° TYP	
Q	0.148	0.158	3.76	4.01
R	0.045	0.055	1.15	1.39
S	0.025	0.035	0.64	0.88
U	0.145	0.155	3.69	3.93
V	0.040	—	1.02	—

- STYLE 1:  
 PIN 1. EMITTER  
 2. COLLECTOR  
 3. BASE

**CASE 77-08  
 TO-225AA TYPE  
 ISSUE V**

## **BD789 BD791 BD790 BD792**

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### **How to reach us:**

**USA / EUROPE:** Motorola Literature Distribution;  
P.O. Box 20912; Phoenix, Arizona 85036. 1-800-441-2447

**MFAX:** RMFAX0@email.sps.mot.com – TOUCHTONE (602) 244-6609  
**INTERNET:** <http://Design-NET.com>

**JAPAN:** Nippon Motorola Ltd.; Tatsumi-SPD-JLDC, Toshikatsu Otsuki,  
6F Seibu-Butsuryu-Center, 3-14-2 Tatsumi Koto-Ku, Tokyo 135, Japan. 03-3521-8315

**HONG KONG:** Motorola Semiconductors H.K. Ltd.; 8B Tai Ping Industrial Park,  
51 Ting Kok Road, Tai Po, N.T., Hong Kong. 852-26629298

